Amendments to the Specification:

Please amend Page 3, beginning line 9, as follows:

After the wafer 25 passing through the chemical mechanical polishing (CMP) process or the etching process, it will moved to the inlet of the measuring system by using the wafer cassette 60 and will be placed on the stage 27 by using a robot 65. Then, the stage 20 is moved to the place under the lens 30 by using the transport device 27 to start measuring the thickness of the wafer. The light is used to irradiate from the lens 30 to the surface of the wafer 25 and the data, which is returned from the light, is showed on the monitor 50. The thickness of the wafer will be known by analyzing the data which is on the monitor ~~500~~.

Please amend Page 8, beginning line 13, as follows:

Before the gas stream environment measuring system begins to operate, the gas supplier 750 must be opened at first ~~to make~~ and supplied the gas passing through the first tube 820 and the second tube 840 and exhausting from the first gas nozzle 400 and the second gas nozzle 450 to form a gas stream 480 in the measuring system. Then the gas extracting apparatus 900 is opened to increase the flowing ability of the gas stream 480 and decide the flowing direction of the gas stream 480. The gas stream 480 will pass through the transport slot 700 and the third tube 800 to the region, which is used to deal with the waste gas, by using the attraction, which produced from the gas-~~attracting~~ extracting apparatus 900 to avoid the gas stream 480 moving to other regions by a way of diffusion in the measuring system. The gas-extracting apparatus 900 comprises a gas-extracting motor or a venture structure. The gas which is used in the gas stream 480 is an inert gas or nitrogen. The gas supplier 750 and the gas-extracting apparatus 900 must be opened continuously in the measuring process. The transport slot 700 is an opening of the measuring system. It is used to collect the gas in the gas stream 480 and used to be the channel to exhaust the gas stream 480

Please amend Page 9, beginning line 14, as follows:

After the wafer 250 passing through the chemical mechanical polishing (CMP) process or the etching process, it will moved to the inlet of the measuring system by using the wafer cassette 600 and will be placed on the stage ~~270~~ 200 by using a robot 650. Then, the stage 200 is moved to the place under the lens 300 by using the transport device 270 to start measuring the thickness of the wafer 250. The light is used to irradiate from the lens 300 to the surface of the wafer 250 and the data, which is returned from the light, is showed on the monitor 50. The thickness of the wafer 250 will be known by analyzing the data which is on the monitor 500.

Please amend page 9, beginning line 25, and carrying over onto page 10, as follows:

Because the material of the wafer is usually formed by using the vapor deposition ways, therefore, the volatility gas will be produced easily in the wafer 250. After passing through the chemical mechanical polishing process or the etching process, the volatility gas will be produced in the wafer 250 more easily. When the wafer 250 is placed on the stage 200 and the stage 200 is moved to the place under the lens 300 by using the transport device 270 to stat measuring the thickness of the wafer 250, the gas which evaporates from the inner wafer 250 will be carried by the gas stream 480, which is exhausted from the second gas nozzle 450, and will make the gas not adhere to the surface of the lens 300 to increase the measuring accuracy. The gas stream 480, which is exhausted from the first gas nozzle 400, can avoid the gas, which evaporates from the inner wafer 250, not to deposit on the datum slice 150 by a way of diffusion to decrease the errors in the lens 300 adjusting process. The gas, which evaporates from the inner wafer 250, will follow with the gas stream 480 passing through the transport slot 700 and the third tube 800 to the region, which is produced from the gas-~~attracting~~ extracting apparatus 900 to avoid the gas stream 480 moving to other regions by a way of diffusion in the measuring system and causing more serious pollution.

Please amend page 10, beginning line 20, and carrying over onto page 4, as follows:

The lens 300 is a precision measuring apparatus in the measuring system. If the present invention gas stream environment measuring system is used, the opportunity of the lens 300 pollution is decreased and the opportunity of cleaning the lens 300 is also decreased. This condition will increase the efficiency of the process and can prevent the cost increasing due to the unsuitable cleaning lens process. In order to increase the measuring accuracy of the lens 300, the lens 300 is usually fixed to prevent the measuring errors due to the shaking. But following the needs of the process, the lens 300 can also fixed on a transport device to increase the efficiency of the measuring system.

Please amend page 11, beginning line 3, as follows:

In the present invention gas stream environment measuring system, controlling the flow rate of the gas stream 480 is important. Therefore, the first flow rate regulating valve 420 is fixed on the first gas nozzle 400 and the second flow rate regulating valve 470 is fixed on the second gas nozzle 450 to control the flow rate of the gas stream 480. if the flow rate of the gas stream 480 is over high, the gas stream 480 will not flow in a fixed direction to the region 950, which is used to deal with the waste gas, by the attraction from the gas-attracting apparatus 900 and will spread by a way of diffusion in the measuring system to cause more serious pollution. If the flow rate of the gas stream 480 is over low, the gas, which evaporates from the inner wafer 250, will still adhere to the surface of the lens 300 easily to cause the errors in the measuring results. Following the needs of the process, the flow rate regulating valve cab also be fixed on the gas supplier 750 or on the first tube 400 and the second tube 450 to control the flow rate of the gas stream 480, which exhausts from the first gas nozzle 400 and the second gas nozzle 450.

Please amend page 12,-beginning line 6, as follows:

In accordance with the present invention, the present invention provides a gas stream environmental measuring system to use the gas stream 480, which is formed by using the exhausted gas from the first gas nozzle 400 and the second gas nozzle 450 to the wafer 250 and the measuring reference point continuously, making the gas, which evaporates from the wafer 250, flow with the gas stream 480 and flow to the outside of the measuring system by using the transport slot 700 and the gas-extracting apparatus 900 to measure the thickness of the wafer 250 successfully and accurately. The flow rate of the gas, which exhausts from the first gas nozzle 400 and the second gas nozzle 450, can be controlled by using the first flow rate regulating valve 420 and the second flow rate regulating valve 470 to avoid the pollution defects in the measuring system due to the flow rate of the gas stream 480 over high or over low. The present invention can also increase the qualities of the products and to decrease the cost of the production. The present invention can further extend the using life of the lens 300 and increase the efficiency of the process.